74AUP1G00

Low-power 2-input NAND gate

Rev. 9.1 — 11 July 2023

Product data sheet

1. General description

The 74AUP1G00 is a single 2-input NAND gate. Schmitt-trigger action at all inputs makes the circuit tolerant of slower input rise and fall times. This device ensures very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V. This device is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- CMOS low power dissipation
- High noise immunity
- Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.65 V to 1.95 V)
 - JESD8-5 (2.3 V to 2.7 V)
 - JESD8C (2.7 V to 3.6 V)
- Low static power consumption; I_{CC} = 0.9 μA (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Overvoltage tolerant inputs to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- · Multiple package options
- ESD protection:
 - HBM: ANSI/ESDA/JEDEC JS-001 class 3A exceeds 5000 V
 - CDM: ANSI/ESDA/JEDEC JS-002 class C3 exceeds 1000 V
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



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3. Ordering information

Table 1. Ordering information

| Type number | Package | | | | | | |
|-------------|-------------------|--------|--|-----------|--|--|--|
| | Temperature range | Name | Description | Version | | | |
| 74AUP1G00GW | -40 °C to +125 °C | TSSOP5 | plastic thin shrink small outline package; 5 leads; body width 1.25 mm | SOT353-1 | | | |
| 74AUP1G00GM | -40 °C to +125 °C | XSON6 | plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm | SOT886 | | | |
| 74AUP1G00GN | -40 °C to +125 °C | XSON6 | extremely thin small outline package; no leads; 6 terminals; body 0.9 × 1.0 × 0.35 mm | SOT1115 | | | |
| 74AUP1G00GS | -40 °C to +125 °C | XSON6 | extremely thin small outline package; no leads; 6 terminals; body 1.0 × 1.0 × 0.35 mm | SOT1202 | | | |
| 74AUP1G00GX | -40 °C to +125 °C | X2SON5 | plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body 0.8 × 0.8 × 0.32 mm | SOT1226-3 | | | |

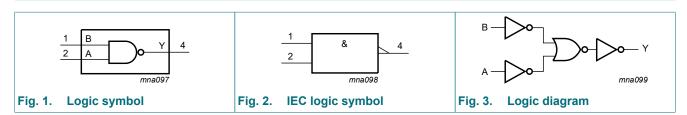
4. Marking

Table 2. Marking

| 10010 - 110110119 | |
|-------------------|------------------|
| Type number | Marking code [1] |
| 74AUP1G00GW | рА |
| 74AUP1G00GM | рА |
| 74AUP1G00GN | рА |
| 74AUP1G00GS | рА |
| 74AUP1G00GX | рА |
| | |

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

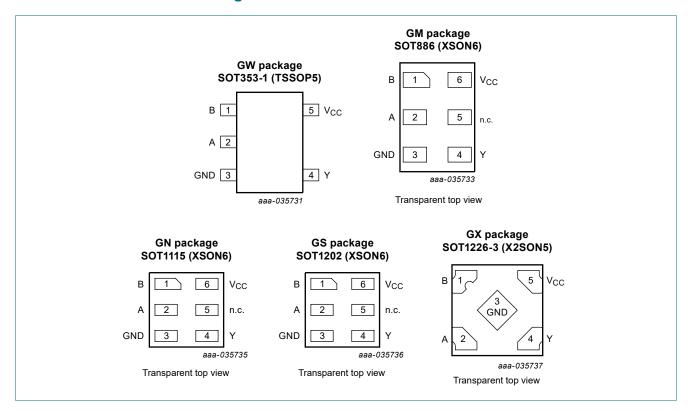


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6. Pinning information

6.1. Pinning



6.2. Pin description

Table 3. Pin description

| Symbol | Pin | Description | |
|-----------------|-------------------|-------------|----------------|
| | TSSOP5 and X2SON5 | XSON6 | |
| В | 1 | 1 | data input |
| A | 2 | 2 | data input |
| GND | 3 | 3 | ground (0 V) |
| Υ | 4 | 4 | data output |
| n.c. | - | 5 | not connected |
| V _{CC} | 5 | 6 | supply voltage |

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7. Functional description

Table 4. Function table

 $H = HIGH \ voltage \ level; \ L = LOW \ voltage \ level.$

| Input | | Output |
|-------|---|--------|
| A | В | Υ |
| L | L | Н |
| L | Н | Н |
| Н | L | Н |
| Н | Н | L |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|-------------------------|--|------|-----------------------|------|
| V_{CC} | supply voltage | | -0.5 | +4.6 | V |
| I _{IK} | input clamping current | V _I < 0 V | -50 | - | mA |
| VI | input voltage | [1] | -0.5 | +4.6 | V |
| I _{OK} | output clamping current | V _O < 0 V | -50 | - | mA |
| V_{O} | output voltage | Active mode [1] | -0.5 | V _{CC} + 0.5 | V |
| | | Power-down mode; V _{CC} = 0 V [1] | -0.5 | +4.6 | V |
| Io | output current | $V_O = 0 V \text{ to } V_{CC}$ | - | ±20 | mA |
| I _{CC} | supply current | | - | +50 | mA |
| I_{GND} | ground current | | -50 | - | mA |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| P _{tot} | total power dissipation | $T_{amb} = -40 ^{\circ}\text{C to } +125 ^{\circ}\text{C}$ [2] | - | 250 | mW |

^[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Recommended operating conditions

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|-------------------------------------|--|-----|-----------------|------|
| V_{CC} | supply voltage | | 0.8 | 3.6 | V |
| VI | input voltage | | 0 | 3.6 | V |
| V _O | output voltage | Active mode | 0 | V _{CC} | V |
| | | Power-down mode; V _{CC} = 0 V | 0 | 3.6 | V |
| T _{amb} | ambient temperature | | -40 | +125 | °C |
| Δt/ΔV | input transition rise and fall rate | V _{CC} = 0.8 V to 3.6 V | 0 | 200 | ns/V |

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^[2] For SOT353-1 (TSSOP5) package: P_{tot} derates linearly with 3.3 mW/K above 74 °C.

For SOT886 (XSON6) package: Ptot derates linearly with 3.3 mW/K above 74 °C.

For SOT1115 (XSON6) package: Ptot derates linearly with 3.2 mW/K above 71 °C.

For SOT1202 (XSON6) package: Ptot derates linearly with 3.3 mW/K above 74 °C.

For SOT1226-3 (X2SON5) package: Ptot derates linearly with 3.0 mW/K above 67 °C.

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10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|---|--|-----------------------|-----|----------------------|------|
| T _{amb} = 2 | 25 °C | | | | | • |
| V _{IH} | HIGH-level input voltage | V _{CC} = 0.8 V | 0.70×V _{CC} | - | - | V |
| | | V _{CC} = 0.9 V to 1.95 V | 0.65×V _{CC} | - | - | V |
| | | V _{CC} = 2.3 V to 2.7 V | 1.6 | - | - | V |
| | | V _{CC} = 3.0 V to 3.6 V | 2.0 | - | - | V |
| V _{IL} | LOW-level input voltage | V _{CC} = 0.8 V | - | - | 0.30×V _{CC} | V |
| | | V _{CC} = 0.9 V to 1.95 V | - | - | 0.35×V _{CC} | V |
| | | V _{CC} = 2.3 V to 2.7 V | - | - | 0.7 | V |
| | | V _{CC} = 3.0 V to 3.6 V | - | - | 0.9 | V |
| V _{OH} | HIGH-level output voltage | $V_I = V_{IH}$ or V_{IL} | | | | |
| | | I_{O} = -20 μ A; V_{CC} = 0.8 V to 3.6 V | V _{CC} - 0.1 | - | - | V |
| | | I _O = -1.1 mA; V _{CC} = 1.1 V | 0.75×V _{CC} | - | - | V |
| | | I _O = -1.7 mA; V _{CC} = 1.4 V | 1.11 | - | - | V |
| | | I _O = -1.9 mA; V _{CC} = 1.65 V | 1.32 | - | - | V |
| | | I _O = -2.3 mA; V _{CC} = 2.3 V | 2.05 | - | - | V |
| | | I _O = -3.1 mA; V _{CC} = 2.3 V | 1.9 | - | - | V |
| | | I _O = -2.7 mA; V _{CC} = 3.0 V | 2.72 | - | - | V |
| | | I _O = -4.0 mA; V _{CC} = 3.0 V | 2.6 | - | - | V |
| V _{OL} | LOW-level output voltage | $V_I = V_{IH}$ or V_{IL} | | | | |
| | | I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V | - | - | 0.1 | V |
| | | I _O = 1.1 mA; V _{CC} = 1.1 V | - | - | 0.3×V _{CC} | V |
| | | I _O = 1.7 mA; V _{CC} = 1.4 V | - | - | 0.31 | V |
| | | I _O = 1.9 mA; V _{CC} = 1.65 V | - | - | 0.31 | V |
| | | I _O = 2.3 mA; V _{CC} = 2.3 V | - | - | 0.31 | V |
| | | I _O = 3.1 mA; V _{CC} = 2.3 V | - | - | 0.44 | V |
| | | I _O = 2.7 mA; V _{CC} = 3.0 V | - | - | 0.31 | V |
| | | I _O = 4.0 mA; V _{CC} = 3.0 V | - | - | 0.44 | V |
| l _l | input leakage current | V_{I} = GND to 3.6 V; V_{CC} = 0 V to 3.6 V | - | - | ±0.1 | μΑ |
| I _{OFF} | power-off leakage current | V_{I} or $V_{O} = 0$ V to 3.6 V; $V_{CC} = 0$ V | - | - | ±0.2 | μΑ |
| Δl _{OFF} | additional power-off leakage current | V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V | - | - | ±0.2 | μΑ |
| I _{CC} | supply current | V_I = GND or V_{CC} ; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V | - | - | 0.5 | μΑ |
| ΔI _{CC} | additional supply current | $V_1 = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$ [1] | - | - | 40 | μΑ |
| Cı | input capacitance | V_{CC} = 0 V to 3.6 V; V_I = GND or V_{CC} | - | 0.8 | - | pF |
| Co | output capacitance | $V_O = GND; V_{CC} = 0 V$ | - | 1.7 | - | pF |

Product data sheet

| Symbo | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|--------------------------------------|--|-----------------------|-----|----------------------|------|
| T _{amb} = . | -40 °C to +85 °C | | | | | |
| V _{IH} | HIGH-level input voltage | V _{CC} = 0.8 V | 0.70×V _{CC} | - | - | V |
| | | V _{CC} = 0.9 V to 1.95 V | 0.65×V _{CC} | - | - | V |
| | | V _{CC} = 2.3 V to 2.7 V | 1.6 | - | - | V |
| | | V _{CC} = 3.0 V to 3.6 V | 2.0 | - | - | V |
| V _{IL} | LOW-level input voltage | V _{CC} = 0.8 V | - | - | 0.30×V _{CC} | V |
| | | V _{CC} = 0.9 V to 1.95 V | - | - | 0.35×V _{CC} | V |
| | | V _{CC} = 2.3 V to 2.7 V | - | - | 0.7 | V |
| | | V _{CC} = 3.0 V to 3.6 V | - | - | 0.9 | V |
| V _{OH} | HIGH-level output voltage | $V_I = V_{IH}$ or V_{IL} | | | | |
| | | $I_O = -20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$ | V _{CC} - 0.1 | - | - | V |
| | | I _O = -1.1 mA; V _{CC} = 1.1 V | 0.7×V _{CC} | - | - | V |
| | | I _O = -1.7 mA; V _{CC} = 1.4 V | 1.03 | - | - | V |
| | | I _O = -1.9 mA; V _{CC} = 1.65 V | 1.30 | - | - | V |
| | | I _O = -2.3 mA; V _{CC} = 2.3 V | 1.97 | - | - | V |
| | | I _O = -3.1 mA; V _{CC} = 2.3 V | 1.85 | - | - | V |
| | | I _O = -2.7 mA; V _{CC} = 3.0 V | 2.67 | - | - | V |
| | | I _O = -4.0 mA; V _{CC} = 3.0 V | 2.55 | - | - | V |
| V _{OL} | LOW-level output voltage | $V_I = V_{IH}$ or V_{IL} | | | | |
| | | I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V | - | - | 0.1 | V |
| | | I _O = 1.1 mA; V _{CC} = 1.1 V | - | - | 0.3×V _{CC} | V |
| | | I _O = 1.7 mA; V _{CC} = 1.4 V | - | - | 0.37 | V |
| | | I _O = 1.9 mA; V _{CC} = 1.65 V | - | - | 0.35 | V |
| | | I _O = 2.3 mA; V _{CC} = 2.3 V | - | - | 0.33 | V |
| | | I _O = 3.1 mA; V _{CC} = 2.3 V | - | - | 0.45 | V |
| | | I _O = 2.7 mA; V _{CC} = 3.0 V | - | - | 0.33 | V |
| | | I _O = 4.0 mA; V _{CC} = 3.0 V | - | - | 0.45 | V |
| l _l | input leakage current | V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V | - | - | ±0.5 | μA |
| I _{OFF} | power-off leakage current | V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V | - | - | ±0.5 | μA |
| Δl _{OFF} | additional power-off leakage current | V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V | - | - | ±0.6 | μA |
| I _{CC} | supply current | V_{I} = GND or V_{CC} ; I_{O} = 0 A; V_{CC} = 0.8 V to 3.6 V | - | - | 0.9 | μA |
| ΔI _{CC} | additional supply current | $V_1 = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$ [1] | - | - | 50 | μA |
| T _{amb} = . | -40 °C to +125 °C | | | | | |
| V _{IH} | HIGH-level input voltage | V _{CC} = 0.8 V | 0.75×V _{CC} | - | - | V |
| | | V _{CC} = 0.9 V to 1.95 V | 0.70×V _{CC} | - | - | V |
| | | V _{CC} = 2.3 V to 2.7 V | 1.6 | - | - | V |
| | | V _{CC} = 3.0 V to 3.6 V | 2.0 | - | - | V |
| V _{IL} | LOW-level input voltage | V _{CC} = 0.8 V | - | - | 0.25×V _{CC} | V |
| | | V _{CC} = 0.9 V to 1.95 V | - | - | 0.30×V _{CC} | V |
| | | V _{CC} = 2.3 V to 2.7 V | - | - | 0.7 | V |
| | | V _{CC} = 3.0 V to 3.6 V | _ | - | 0.9 | V |

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| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-------------------|---|--|------------------------|-----|----------------------|------|
| V _{OH} | HIGH-level output voltage | $V_I = V_{IH}$ or V_{IL} | | | | |
| | | I _O = -20 μA; V _{CC} = 0.8 V to 3.6 V | V _{CC} - 0.11 | - | - | V |
| | | I _O = -1.1 mA; V _{CC} = 1.1 V | 0.6×V _{CC} | - | - | V |
| | | I _O = -1.7 mA; V _{CC} = 1.4 V | 0.93 | - | - | V |
| | | I _O = -1.9 mA; V _{CC} = 1.65 V | 1.17 | - | - | V |
| | | I _O = -2.3 mA; V _{CC} = 2.3 V | 1.77 | - | - | V |
| | | I _O = -3.1 mA; V _{CC} = 2.3 V | 1.67 | - | - | V |
| | | I _O = -2.7 mA; V _{CC} = 3.0 V | 2.40 | - | - | V |
| | | I _O = -4.0 mA; V _{CC} = 3.0 V | 2.30 | - | - | V |
| V _{OL} | LOW-level output voltage | V _I = V _{IH} or V _{IL} | | | | |
| | | I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V | - | - | 0.11 | V |
| | | I _O = 1.1 mA; V _{CC} = 1.1 V | - | - | 0.33×V _{CC} | V |
| | | I _O = 1.7 mA; V _{CC} = 1.4 V | - | - | 0.41 | V |
| | | I _O = 1.9 mA; V _{CC} = 1.65 V | - | - | 0.39 | V |
| | | I _O = 2.3 mA; V _{CC} = 2.3 V | - | - | 0.36 | V |
| | | I _O = 3.1 mA; V _{CC} = 2.3 V | - | - | 0.50 | V |
| | | I _O = 2.7 mA; V _{CC} = 3.0 V | - | - | 0.36 | V |
| | | I _O = 4.0 mA; V _{CC} = 3.0 V | - | - | 0.50 | V |
| l _l | input leakage current | V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V | - | - | ±0.75 | μΑ |
| I _{OFF} | power-off leakage current | V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V | - | - | ±0.75 | μΑ |
| Δl _{OFF} | additional power-off leakage current | V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V | - | - | ±0.75 | μΑ |
| I _{CC} | supply current | V_I = GND or V_{CC} ; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V | - | - | 1.4 | μΑ |
| Δl _{CC} | additional supply current | $V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$ [1] | - | - | 75 | μA |

^[1] One input at V_{CC} - 0.6 V, other input at V_{CC} or GND.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 5

| Symbol | Parameter | Conditions | Min | Typ [1] | Max | Unit | | |
|---|-------------------|------------------------------------|-----|---------|------|------|--|--|
| T _{amb} = 25 °C; C _L = 5 pF | | | | | | | | |
| t _{pd} | propagation delay | A, B to Y; see <u>Fig. 4</u> [2] | | | | | | |
| | | V _{CC} = 0.8 V | - | 17.5 | - | ns | | |
| | | V _{CC} = 1.1 V to 1.3 V | 2.5 | 5.3 | 11.0 | ns | | |
| | | V _{CC} = 1.4 V to 1.6 V | 2.0 | 3.8 | 6.8 | ns | | |
| | | V _{CC} = 1.65 V to 1.95 V | 1.6 | 3.1 | 5.3 | ns | | |
| | | V _{CC} = 2.3 V to 2.7 V | 1.3 | 2.5 | 4.0 | ns | | |
| | | V _{CC} = 3.0 V to 3.6 V | 1.0 | 2.2 | 3.6 | ns | | |

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| Symbo | ol Parameter | Conditions | | Min | Typ [1] | Max | Unit |
|--------------------|-------------------------------|--|----------|-----|---------|------|--------|
| T _{amb} = | 25 °C; C _L = 10 pF | | <u>'</u> | | | | |
| t _{pd} | propagation delay | A, B to Y; see Fig. 4 | [2] | | | | |
| | | V _{CC} = 0.8 V | | - | 21.0 | - | ns |
| | | V _{CC} = 1.1 V to 1.3 V | | 2.4 | 6.1 | 13.0 | ns |
| | | V _{CC} = 1.4 V to 1.6 V | | 2.4 | 4.4 | 7.9 | ns |
| | | V _{CC} = 1.65 V to 1.95 V | | 2.0 | 3.7 | 6.2 | ns |
| | | V _{CC} = 2.3 V to 2.7 V | | 1.4 | 3.0 | 4.7 | ns |
| | | V _{CC} = 3.0 V to 3.6 V | | 1.3 | 2.8 | 4.3 | ns |
| T _{amb} = | 25 °C; C _L = 15 pF | | <u> </u> | | | | |
| t _{pd} | propagation delay | A, B to Y; see Fig. 4 | [2] | | | | |
| | | V _{CC} = 0.8 V | | - | 24.5 | - | ns |
| | | V _{CC} = 1.1 V to 1.3 V | | 3.4 | 6.9 | 14.8 | ns |
| | | V _{CC} = 1.4 V to 1.6 V | | 2.8 | 5.0 | 8.9 | ns |
| | | V _{CC} = 1.65 V to 1.95 V | | 2.0 | 4.1 | 7.0 | ns |
| | | V _{CC} = 2.3 V to 2.7 V | | 1.7 | 3.5 | 5.3 | ns |
| | | V _{CC} = 3.0 V to 3.6 V | | 1.6 | 3.2 | 4.9 | ns |
| T _{amb} = | 25 °C; C _L = 30 pF | | | | | | |
| t _{pd} | propagation delay | A, B to Y; see Fig. 4 | [2] | | | | \top |
| | | V _{CC} = 0.8 V | | - | 34.8 | - | ns |
| | | V _{CC} = 1.1 V to 1.3 V | | 4.6 | 9.2 | 20.1 | ns |
| | | V _{CC} = 1.4 V to 1.6 V | | 3.0 | 6.5 | 11.8 | ns |
| | | V _{CC} = 1.65 V to 1.95 V | | 2.6 | 5.4 | 9.3 | ns |
| | | V _{CC} = 2.3 V to 2.7 V | | 2.4 | 4.6 | 7.1 | ns |
| | | V _{CC} = 3.0 V to 3.6 V | | 2.3 | 4.3 | 6.5 | ns |
| T _{amb} = | 25 °C | | | | | | |
| C _{PD} | power dissipation | $f = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$ | [3] | | | | |
| | capacitance | V _{CC} = 0.8 V | | - | 2.6 | - | pF |
| | | V _{CC} = 1.1 V to 1.3 V | | - | 2.8 | - | pF |
| | | V _{CC} = 1.4 V to 1.6 V | | - | 2.9 | - | pF |
| | | V _{CC} = 1.65 V to 1.95 V | | - | 3.1 | - | pF |
| | | V _{CC} = 2.3 V to 2.7 V | | - | 3.6 | - | pF |
| | | V _{CC} = 3.0 V to 3.6 V | | - | 4.2 | - | pF |
| | | | | | | | |

^[1] All typical values are measured at nominal V_{CC} .

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

 ^[2] t_{pd} is the same as t_{PLH} and t_{PHL}.
 [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 P_D = C_{PD} × V_{CC}² × f_i × N + Σ(C_L × V_{CC}² × f_o) where:

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Table 9. Dynamic characteristics

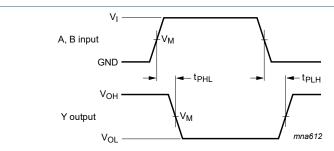
Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 5

| Symbol | Parameter | Conditions | -40 °C t | o +85 °C | -40 °C to | +125 °C | Unit |
|----------------------|-------------------|------------------------------------|----------|----------|-----------|---------|------|
| | | | Min | Max | Min | Max | |
| C _L = 5 p | F | | | | | | |
| t _{pd} | propagation delay | A, B to Y; see <u>Fig. 4</u> [1] | | | | | |
| | | V _{CC} = 1.1 V to 1.3 V | 2.1 | 12.2 | 2.1 | 13.5 | ns |
| | | V _{CC} = 1.4 V to 1.6 V | 1.8 | 7.8 | 1.8 | 8.6 | ns |
| | | V _{CC} = 1.65 V to 1.95 V | 1.4 | 6.2 | 1.4 | 6.9 | ns |
| | | V _{CC} = 2.3 V to 2.7 V | 1.1 | 4.7 | 1.1 | 5.2 | ns |
| | | V _{CC} = 3.0 V to 3.6 V | 1.0 | 4.2 | 1.0 | 4.7 | ns |
| C _L = 10 | pF | | | | | | |
| t _{pd} | propagation delay | A, B to Y; see <u>Fig. 4</u> [1] | | | | | |
| | | V _{CC} = 1.1 V to 1.3 V | 2.2 | 14.4 | 2.2 | 15.9 | ns |
| | | V _{CC} = 1.4 V to 1.6 V | 2.2 | 9.2 | 2.2 | 10.2 | ns |
| | | V _{CC} = 1.65 V to 1.95 V | 1.9 | 7.3 | 1.9 | 8.1 | ns |
| | | V _{CC} = 2.3 V to 2.7 V | 1.3 | 5.6 | 1.3 | 6.2 | ns |
| | | V _{CC} = 3.0 V to 3.6 V | 1.2 | 4.9 | 1.2 | 5.4 | ns |
| C _L = 15 | pF | | | | | | |
| t _{pd} | propagation delay | A, B to Y; see <u>Fig. 4</u> [1] | | | | | |
| | | V _{CC} = 1.1 V to 1.3 V | 3.1 | 16.5 | 3.1 | 18.2 | ns |
| | | V _{CC} = 1.4 V to 1.6 V | 2.5 | 10.5 | 2.5 | 11.6 | ns |
| | | V _{CC} = 1.65 V to 1.95 V | 2.0 | 8.3 | 2.0 | 9.2 | ns |
| | | V _{CC} = 2.3 V to 2.7 V | 1.5 | 6.4 | 1.5 | 7.1 | ns |
| | | V _{CC} = 3.0 V to 3.6 V | 1.4 | 5.7 | 1.4 | 6.3 | ns |
| C _L = 30 | pF | | | | | | |
| t _{pd} | propagation delay | A, B to Y; see <u>Fig. 4</u> [1] | | | | | |
| | | V _{CC} = 1.1 V to 1.3 V | 4.1 | 22.6 | 4.1 | 24.9 | ns |
| | | V _{CC} = 1.4 V to 1.6 V | 2.9 | 14.0 | 2.9 | 15.4 | ns |
| | | V _{CC} = 1.65 V to 1.95 V | 2.3 | 11.1 | 2.3 | 12.3 | ns |
| | | V _{CC} = 2.3 V to 2.7 V | 2.1 | 8.5 | 2.1 | 9.4 | ns |
| | | V _{CC} = 3.0 V to 3.6 V | 2.1 | 7.6 | 2.1 | 8.4 | ns |

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

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11.1. Waveforms and test circuit



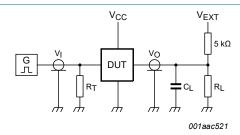
Measurement points are given in Table 10.

Logic levels: V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig. 4. The data input (A or B) to output (Y) propagation delays

Table 10. Measurement points

| Supply voltage | Input | Output | | |
|-----------------|-----------------------|-----------------|-------------|-----------------------|
| V _{CC} | V_{M} | V _I | $t_r = t_f$ | V_{M} |
| 0.8 V to 3.6 V | 0.5 × V _{CC} | V _{CC} | ≤ 3.0 ns | 0.5 × V _{CC} |



Test data is given in <u>Table 11</u>.

Definitions for test circuit:

R_L = Load resistance;

C_L = Load capacitance including jig and probe capacitance;

 R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator;

V_{EXT} = External voltage for measuring switching times.

Fig. 5. Test circuit for measuring switching times

Table 11. Test data

| Supply voltage | Load | | V _{EXT} | | |
|-----------------|------------------------------|--------------------|-------------------------------------|-------------------------------------|-------------------------------------|
| V _{CC} | C _L | R _L [1] | t _{PLH} , t _{PHL} | t _{PZH} , t _{PHZ} | t _{PZL} , t _{PLZ} |
| 0.8 V to 3.6 V | 5 pF, 10 pF, 15 pF and 30 pF | 5 kΩ or 1 MΩ | open | GND | 2 × V _{CC} |

[1] For measuring enable and disable times R_L = 5 k Ω . For measuring propagation delays, setup and hold times and pulse width R_L = 1 M Ω .

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12. Package outline

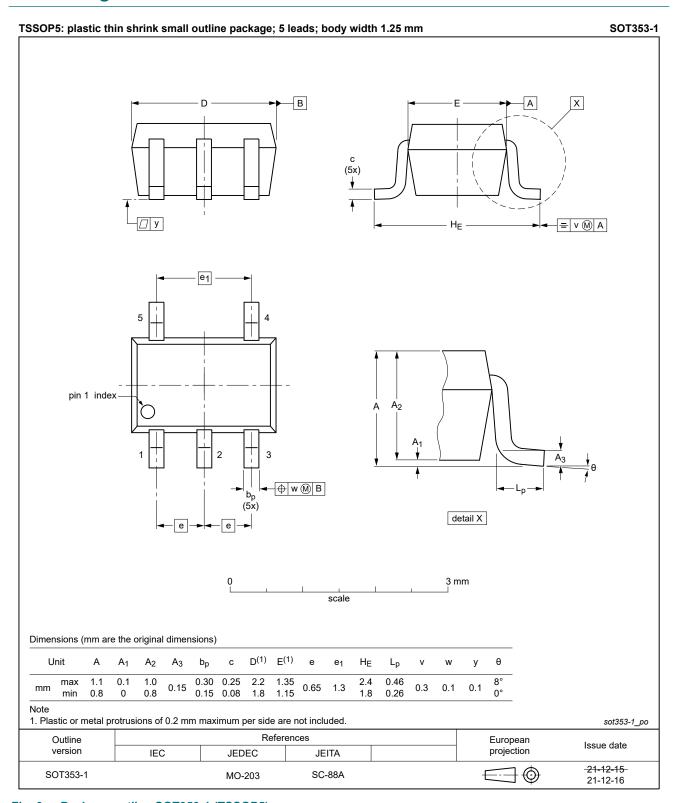


Fig. 6. Package outline SOT353-1 (TSSOP5)

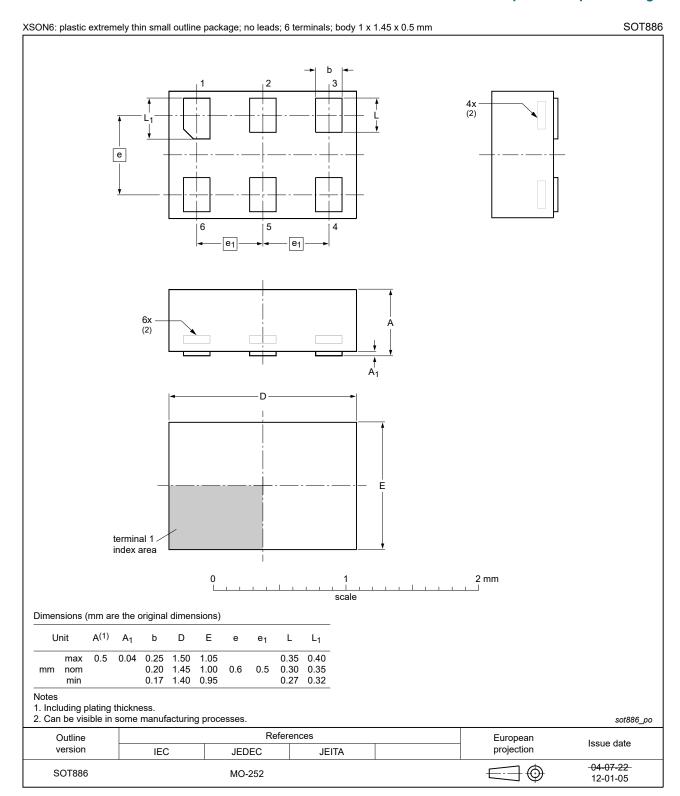


Fig. 7. Package outline SOT886 (XSON6)

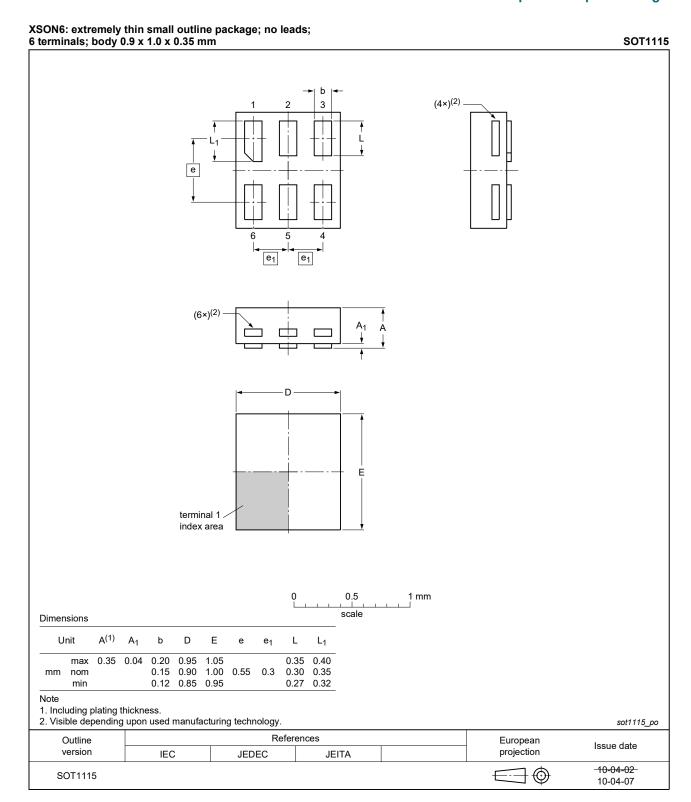


Fig. 8. Package outline SOT1115 (XSON6)

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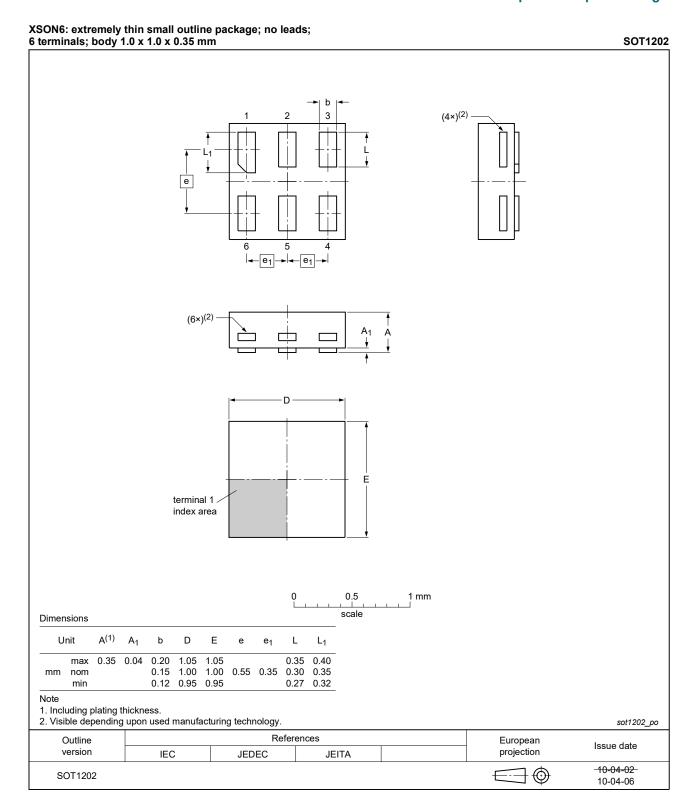


Fig. 9. Package outline SOT1202 (XSON6)

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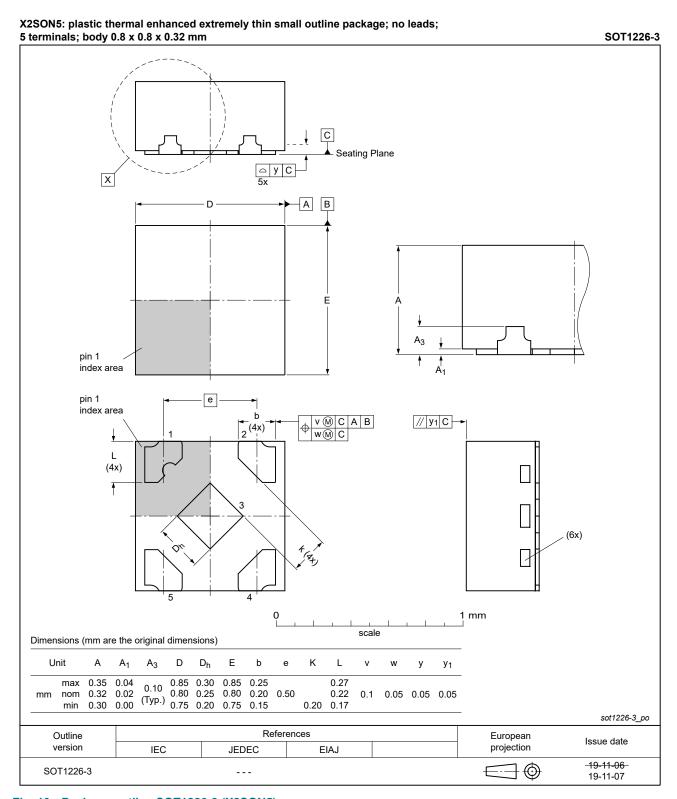


Fig. 10. Package outline SOT1226-3 (X2SON5)

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13. Abbreviations

Table 12. Abbreviations

| Acronym | Description | |
|---------|-------------------------|--|
| CDM | Charged Device Model | |
| DUT | Device Under Test | |
| ESD | ElectroStatic Discharge | |
| НВМ | Human Body Model | |

14. Revision history

Table 13. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes | | |
|-----------------|---|---|---------------|---------------|--|--|
| 74AUP1G00 v.9.1 | 20230711 | Product data sheet | - | 74AUP1G00 v.8 | | |
| Modifications: | Section 2: E | <u>Section 2</u> : ESD specification updated according to the latest JEDEC standard. | | | | |
| 74AUP1G00 v.8 | 20220113 | 20220113 Product data sheet - 74AUP1G00 v.7 | | | | |
| Modifications: | <u>Table 5</u>: DerType numbeSOT1226 (X | Section 1 and Section 2 updated. Table 5: Derating values for P_{tot} total power dissipation updated. Type number 74AUP1G00GF (SOT891) removed. SOT1226 (X2SON5) package changed to SOT1226-3 (X2SON5) package. Fig. 6: Package outline drawing for SOT353-1 (TSSOP5) has changed. | | | | |
| 74AUP1G00 v.7 | 20190423 | Product data sheet | - | 74AUP1G00 v.6 | | |
| Modifications: | of Nexperia. • Legal texts h | The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Pin configuration drawing SOT1226 (X2SON5) updated. | | | | |
| 74AUP1G00 v.6 | 20120627 | Product data sheet | - | 74AUP1G00 v.5 | | |
| Modifications: | Added type | Added type number 74AUP1G00GX (SOT1226). | | | | |
| 74AUP1G00 v.5 | 20120316 | Product data sheet | - | 74AUP1G00 v.4 | | |
| Modifications: | Package out | Package outline drawing of SOT886 (<u>Fig. 7</u>) modified. | | | | |
| 74AUP1G00 v.4 | 20111115 | Product data sheet | - | 74AUP1G00 v.3 | | |
| Modifications: | Legal pages | Legal pages updated. | | | | |
| 74AUP1G00 v.3 | 20101007 | Product data sheet | - | 74AUP1G00 v.2 | | |
| 74AUP1G00 v.2 | 20060629 | Product data sheet | - | 74AUP1G00 v.1 | | |
| 74AUP1G00 v.1 | 20050711 | Product data sheet | - | - | | |

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15. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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